Amendments to the Claims:

This listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims:

Claims 1-32 (canceled)

Claim 33 (original): A semiconductor light-emitting device comprising:

a substrate including a substrate surface positioned along a substrate surface plane;

a crystal layer comprising an approximately hexagonal prismoid, having a face oriented about an S- plane, and a top region oriented about a C-plane; and

a layer of a first conductivity type, an active layer, and a layer of a second conductivity type each formed along at least a portion of the approximately hexagonal prismoid.

Claims 34-82 (canceled)

Claim 83 (new): A semiconductor light-emitting device comprising:

a substrate including a substrate surface positioned along a surface plane;

a crystal layer including a crystal surface oriented along a crystal surface plane diagonally intersecting the substrate surface plane; and

a first conductive layer, an active layer, and a second conductive layer each formed along at least a portion of the crystal surface, wherein the crystal surface plane comprises a plane having a plane orientation inclined at an angle ranging from about 5 to about 6 degrees with respect to at least one of a S-plane and a (11-22) plane.

Claim 84 (new): A semiconductor light-emitting device comprising:

a substrate including a substrate surface positioned along a substrate surface plane;

a crystal layer comprising an approximately hexagonal pyramid, having a face oriented along an S-plane that diagonally intersects the substrate surface plane; and

a layer of a first conductivity type, an active layer, and a layer of a second conductivity type each formed along at least a portion of the approximately hexagonal pyramid, wherein a current is injected into the active layer such that a current density is lower near or at an apex of the approximately hexagonal pyramid than in the face of the approximately hexagonal pyramid.

Claim 85 (new): A semiconductor light-emitting device comprising:

a substrate including a substrate surface positioned along a substrate surface plane;

a crystal grown layer formed by selective growth and including a crystal surface oriented along a crystal surface plane diagonally intersecting the substrate surface plane;

an active layer which is formed along at least a portion of the crystal grown layer that emits light upon injection of an amount of current;

and a reflecting region which is formed substantially parallel to the crystal surface plane and reflects at least a portion of the light emerging from the active layer, wherein the active layer is approximately parallel to a plane having a plane orientation inclined at an angle ranging from about 5 to about 6 degrees with respect to at least one of a S-plane and a (11-22) plane.

Claim 86 (new): A semiconductor light-emitting device comprising:

a substrate;

a crystal layer including a crystal surface oriented along a crystal surface plane diagonally intersecting a substrate surface plane; and

a first conductive layer, an active layer, and a second conductive layer, each parallel to said crystal layer and each formed along at least a portion of said crystal surface, wherein the shape of the crystal layer is a pyramid.

Claim 87 (new): The semiconductor light-emitting device as claimed in claim 86, wherein the shape of the crystal layer is a hexagonal-pyramid.

Claim 88 (new): The semiconductor light-emitting device as claimed in claim 86, wherein the crystal layer comprises a wurtzite crystal structure.

Claim 89 (new): The semiconductor light-emitting device as claimed in claim 86, wherein the crystal layer is composed of a nitride semiconductor material.

Claim 90 (new): The semiconductor light-emitting device as claimed in claim 86, wherein the crystal layer is formed by selective growth on the substrate with a material layer capable of growth interposed therebetween.

Claim 91 (new): The semiconductor light-emitting device as claimed in claim 90, wherein the material layer capable of growth is selectively removed during selective growth to form the crystal layer.

Claim 92 (new): The semiconductor light-emitting device as claimed in claim 90, wherein the semiconductor light-emitting device further comprises a masking layer having an opening through which the crystal layer is selectively grown.

Claim 93 (new): The semiconductor light-emitting device as claimed in claim 92, wherein the crystal layer is formed by selective growth such that the crystal layer extends laterally from the opening in the masking layer.

Claim 94 (new): The semiconductor light-emitting device as claimed in claim 86, wherein the substrate plane comprises a C-plane.

Claim 95 (new): The semiconductor light-emitting device as claimed in claim 86, wherein the crystal surface plane comprises at least one of a S-plane and a (11-22) plane.

Claim 96 (new): The semiconductor light-emitting device as claimed in claim 86, wherein a current is injected into the active layer.

Claim 97 (new): The semiconductor light-emitting device as claimed in claim 86, wherein the active layer comprises InGaN.

Claim 98 (new): A semiconductor light-emitting device comprising:

a substrate including a substrate surface plane;

a mask on the substrate, said mask including an opening;

a crystal layer positioned on the opening of the mask, said crystal layer including a crystal surface oriented along a crystal surface plane diagonally intersecting the substrate surface plane; and

a first conductive layer, an active layer, and a second conductive layer, wherein said first conductive layer, said active layer and said second conductive layer are each parallel to said crystal layer, are each formed along at least a portion of said crystal surface, and each terminate at the mask.

Claim 99 (new): The semiconductor light-emitting device as claimed in claim 98, wherein the mask is an insulate mask.

Claim 100 (new): The semiconductor light-emitting device as claimed in claim 98, wherein the mask includes a ring opening.

Claim 101 (new): The semiconductor light-emitting device as claimed in claim 98, wherein the crystal layer comprises a wurtzite crystal structure.

Claim 102 (new): The semiconductor light-emitting device as claimed in claim 98, wherein the crystal layer is composed of a nitride semiconductor material.

Claim 103 (new): The semiconductor light-emitting device as claimed in claim 98, wherein the crystal layer is formed by selective growth on the substrate with a material layer capable of growth interposed therebetween.

Claim 104 (new): The semiconductor light-emitting device as claimed in claim 103, wherein the material layer capable of growth is selectively removed during selective growth to form the crystal layer.

Claim 105 (new): The semiconductor light-emitting device as claimed in claim 98, wherein the substrate surface plane comprises a C-plane.

Claim 106 (new): The semiconductor light-emitting device as claimed in claim 98, wherein the crystal surface plane comprises at least one of a S-plane and a (11-22) plane.

Claim 107 (new): The semiconductor light-emitting device as claimed in claim 98, wherein the active layer comprises InGaN.